

# NTJD4152P

## Trench Small Signal MOSFET

20 V, 0.88 A, Dual P-Channel, ESD Protected SC-88

### Features

- Leading Trench Technology for Low  $R_{DS(ON)}$  Performance
- Small Footprint Package (SC70-6 Equivalent)
- ESD Protected Gate
- This is a Pb-Free Device

### Applications

- Load/Power Management
- Charging Circuits
- Load Switching
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	-20	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 12$	V	
Continuous Drain Current (Note 1)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	-0.88	A
			$T_A = 85^\circ\text{C}$	-0.63	
Power Dissipation (Note 1)	Steady State	$P_D$	$T_A = 25^\circ\text{C}$	0.272	W
			$T_A = 85^\circ\text{C}$	0.141	
Continuous Drain Current (Note 2)	$t \leq 5$ s	$I_D$	$T_A = 25^\circ\text{C}$	-1.0	A
			$T_A = 85^\circ\text{C}$	-0.72	
Power Dissipation (Note 2)	$t \leq 5$ s	$P_D$	$T_A = 25^\circ\text{C}$	0.35	W
			$T_A = 85^\circ\text{C}$	0.181	
Pulsed Drain Current		$I_{DM}$	$\pm 3.0$	A	
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	
Continuous Source Current (Body Diode)		$I_S$	-0.48	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

### THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	460	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s	$R_{\theta JA}$	357	
Junction-to-Lead – Steady State	$R_{\theta JL}$	226	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

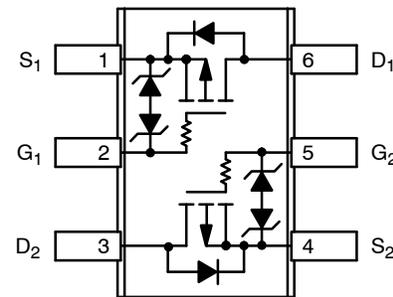
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces), steady state.
2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces),  $t \leq 5$  s.



ON Semiconductor®

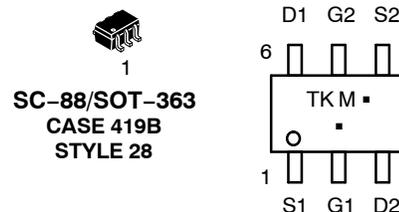
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
-20 V	215 m $\Omega$ @ -4.5 V	-0.88 A
	345 m $\Omega$ @ -2.5 V	
	600 m $\Omega$ @ -1.8 V	



Top View

### MARKING DIAGRAM & PIN ASSIGNMENT



SC-88/SOT-363  
CASE 419B  
STYLE 28

TK = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping
NTJD4152PT1G	SOT-363 (Pb-Free)	3000 Units/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 125°C		1.0	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			0.03	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V			6.0	

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250 μA	-0.45		1.2	V	
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.88 A			215	mΩ	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -0.71 A			345		500
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -0.20 A			600		1000
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.88 A			3.0	S	

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -20 V			155	pF
Output Capacitance	C <sub>OSS</sub>				25	
Reverse Transfer Capacitance	C <sub>RSS</sub>				18	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.88 A			2.2	nC
Gate-to-Source Charge	Q <sub>GS</sub>				0.5	
Gate-to-Drain Charge	Q <sub>GD</sub>				0.65	

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.5 A, R <sub>G</sub> = 20 Ω			5.8	ns
Rise Time	t <sub>r</sub>				6.5	
Turn-Off Delay Time	t <sub>d(OFF)</sub>				13.5	
Fall Time	t <sub>f</sub>				3.5	

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -0.48 A	T <sub>J</sub> = 25°C		-0.8	-1.2	V
			T <sub>J</sub> = 125°C		-0.66		

3. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

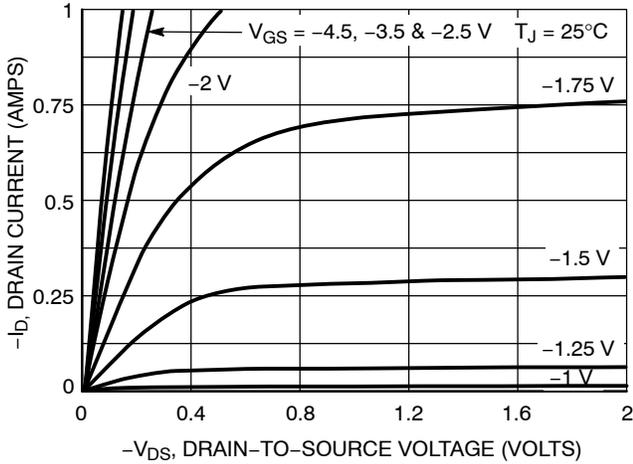


Figure 1. On-Region Characteristics

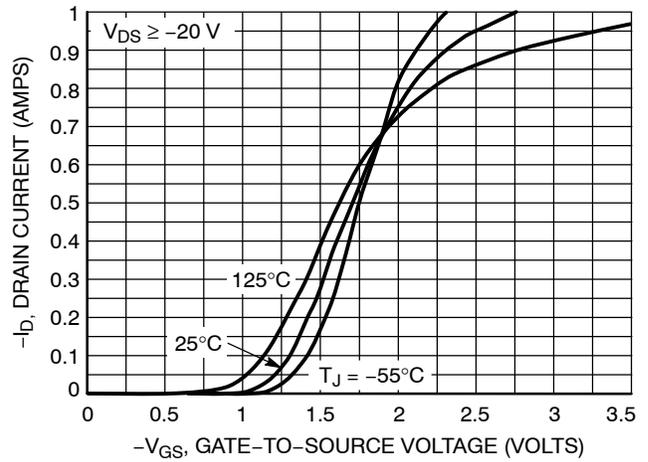


Figure 2. Transfer Characteristics

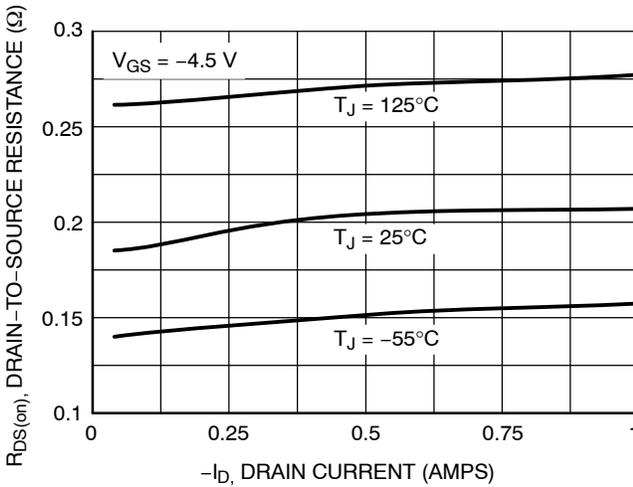


Figure 3. On-Resistance vs. Drain Current and Temperature

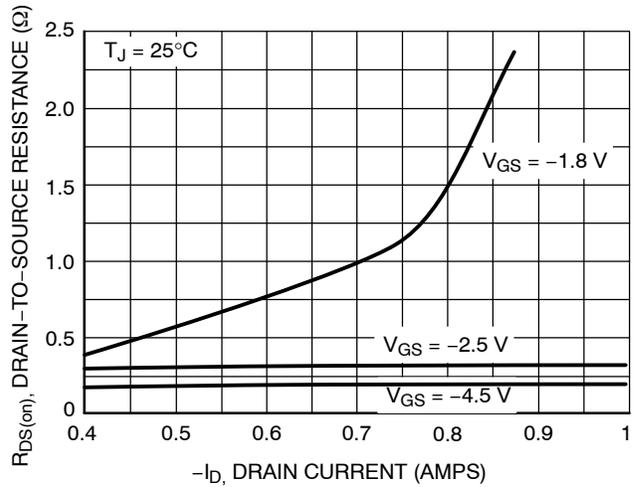


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

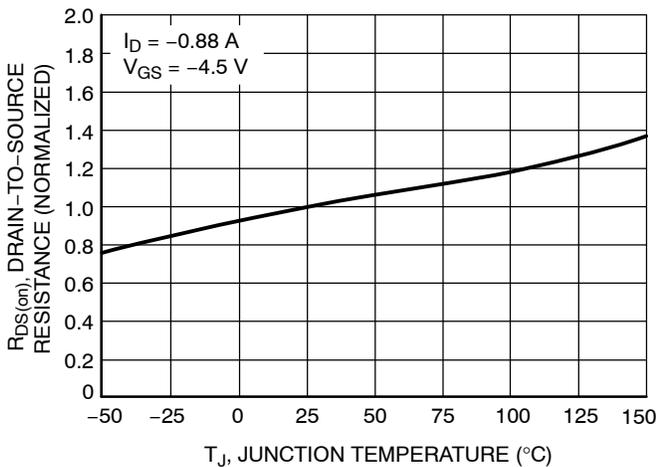


Figure 5. On-Resistance Variation with Temperature

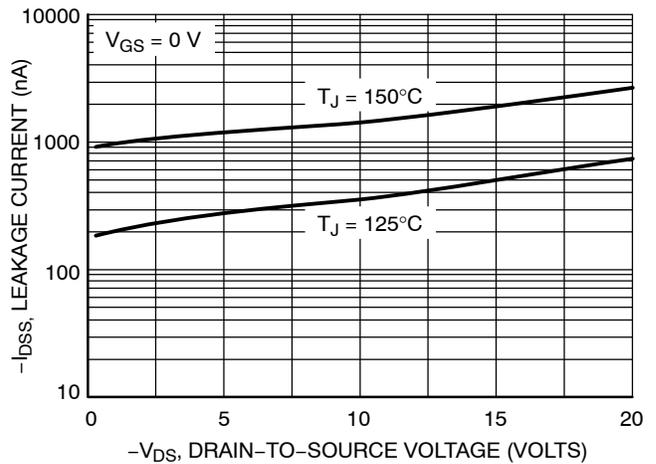


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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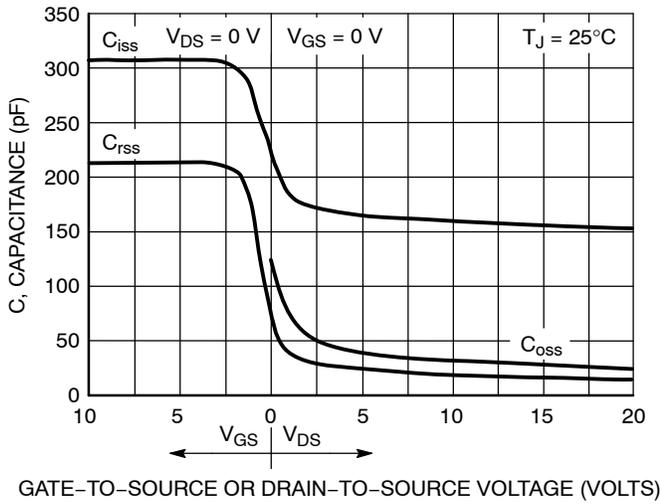


Figure 7. Capacitance Variation

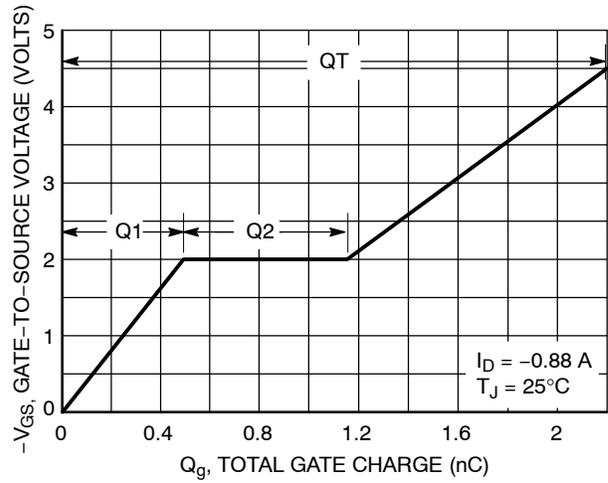


Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

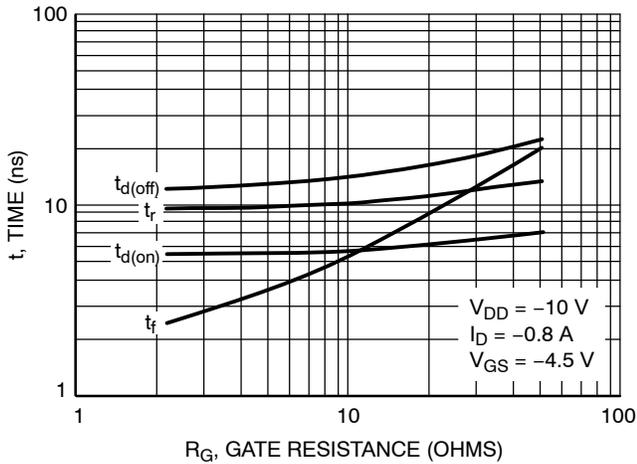


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

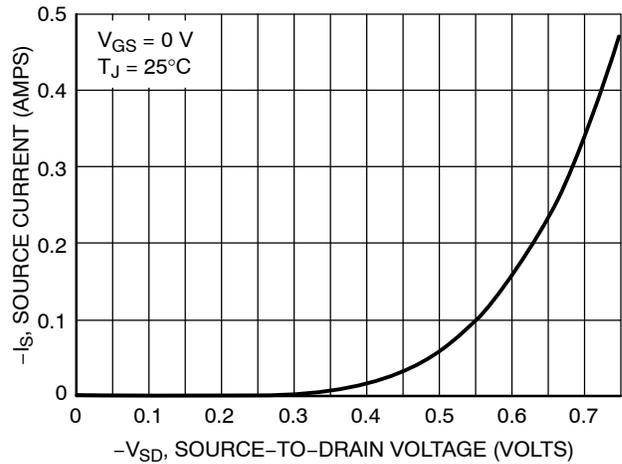
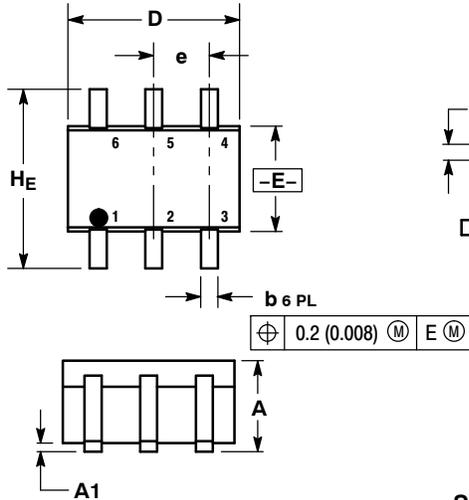


Figure 10. Diode Forward Voltage vs. Current

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## PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363  
CASE 419B-02  
ISSUE W



**NOTES:**

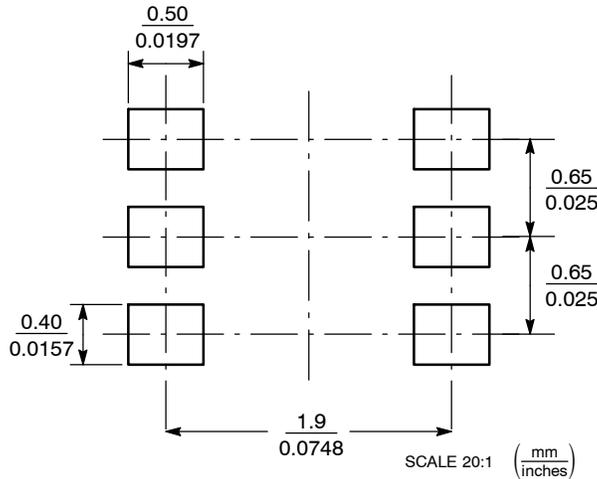
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

**STYLE 26:**

- PIN 1. SOURCE 1
- GATE 1
- DRAIN 2
- SOURCE 2
- GATE 2
- DRAIN 1

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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